

Silicon PNP Power Transistor

BDW52/A/B/C

DESCRIPTION

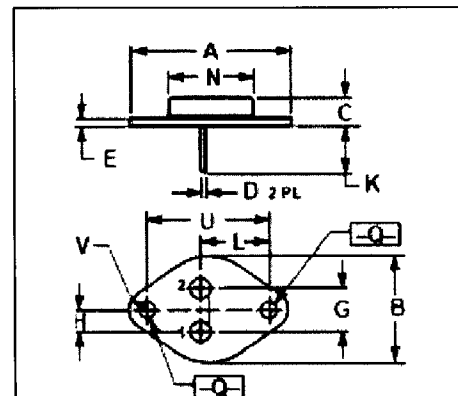
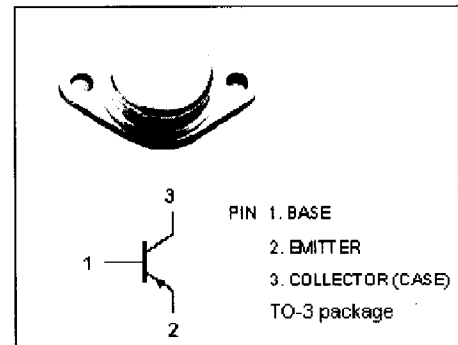
- Collector Current $-I_C = -15A$
- Collector-Emitter Sustaining Voltage-
 $V_{CEO(SUS)} = -45V(\text{Min})-$ BDW52; $-60V(\text{Min})-$ BDW52A
 $-80V(\text{Min})-$ BDW52B; $-100V(\text{Min})-$ BDW52C
- Complement to Type BDW51/A/B/C

APPLICATIONS

- Designed for use in power linear and switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

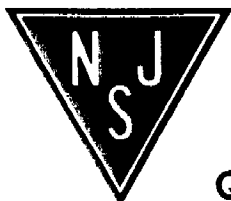
SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	BDW52	-45
		BDW52A	-60
		BDW52B	-80
		BDW52C	-100
V_{CEO}	Collector-Emitter Voltage	BDW52	-45
		BDW52A	-60
		BDW52B	-80
		BDW52C	-100
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_{CM}	Collector Current-Peak	-20	A
I_B	Base Current	-7	A
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	125	W
T_J	Junction Temperature	200	$^\circ C$
T_{stg}	Storage Temperature Range	-65~200	$^\circ C$



DIM	mm	
	MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.4	$^\circ C/W$



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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sus)}$	Collector-Emitter Sustaining Voltage	BDW52	$I_C = -100\text{mA}; I_B = 0$			V
		BDW52A		-45		
		BDW52B		-60		
		BDW52C		-80		
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -0.5\text{A}$			-1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -10\text{A}; I_B = -2.5\text{A}$			-3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -10\text{A}; I_B = -2.5\text{A}$			-2.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -5\text{A}; V_{CE} = -4\text{V}$			-1.5	V
I_{CBO}	Collector Cutoff Current	BDW52	$V_{CB} = -45\text{V}; I_E = 0$ $V_{CB} = -45\text{V}; I_E = 0; T_C = 150^\circ\text{C}$			mA
		BDW52A		-0.5		
		BDW52B		-0.5		
		BDW52C		-0.5		
I_{CEO}	Collector Cutoff Current	BDW52	$V_{CE} = -22\text{V}; I_B = 0$			mA
		BDW52A		-1.0		
		BDW52B		-1.0		
		BDW52C		-1.0		
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-2.0	mA
h_{FE-1}	DC Current Gain	$I_C = -5\text{A}; V_{CE} = -4\text{V}$	20		150	
h_{FE-2}	DC Current Gain	$I_C = -10\text{A}; V_{CE} = -4\text{V}$	5			
f_T	Current Gain-Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -4\text{V}$	3			MHz